

# SANYO Semiconductors DATA SHEET

# LB11946 — Monolithic Digital IC PWM Current Control Stepping Motor Driver

#### Overview

The LB11946 is a stepping motor driver IC that implements PWM current control bipolar drive with a fixed off time. This IC features 15 current setting levels using a fixed VREF voltage and support for microstepping drive from 1-2 phase excitation drive to 4W1-2 phase excitation drive. This device is optimal for driving stepping motors such as those used for carriage drive and paper feed in printers.

#### **Features**

- PWM current control (with a fixed off time)
- Logic input serial-parallel converter (allows 1-2, W1-2, 2W1-2, and 4W1-2 phase excitation drive)
- Current attenuation switching function (with slow decay, fast decay, and mixed decay modes)
- Built-in upper and lower side diodes
- Simultaneous on state prevention function (through current prevention)
- Noise canceller function
- Thermal shutdown circuit
- Shutoff on low logic system voltage circuit
- Low-power mode control pin

#### **Specifications**

#### **Absolute Maximum Ratings** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Motor supply voltage	VBB		50	V
Peak output current	I <sub>O</sub> peak	tw ≤ 20 μS	1.2	Α
Continuous output current	I <sub>O</sub> max		1.0	Α
Logic system supply voltage	Vcc		7.0	V
Logic input voltage range	V <sub>IN</sub>		−0.3 to V <sub>CC</sub>	V
Emitter output voltage	VE	V <sub>CC</sub> = 5 V specifications	1.0	V
Emilier output voltage	VE	V <sub>CC</sub> = 3.3 V specifications	0.5	V
Allowable power dissipation (IC internal)	Pdmax	Ta = 25°C, independent IC	3.0	W
Operating temperature	Topr		-20 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

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# LB11946

# Recommended Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Motor supply voltage	$V_{BB}$		10 to 45	V
Logic system supply voltage	Vac	V <sub>CC</sub> = 5 V specifications	4.5 to 5.5	٧
	V <sub>CC</sub>	V <sub>CC</sub> = 3.3 V specifications	3.0 to 3.6	>
Reference voltage	\/	V <sub>CC</sub> = 5 V specifications	0.0 to 3.0	>
	V <sub>REF</sub>	V <sub>CC</sub> = 3.3 V specifications	0.0 to 1.0	V

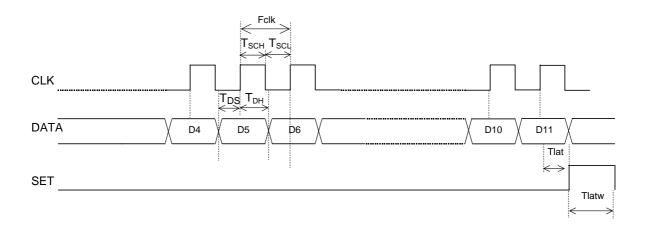
# **Electrical Characteristics** at $Ta = 25^{\circ}C$ , $V_{CC} = 5$ V, $V_{BB} = 42$ V, $V_{REF} = 1.52$ V

Parameter	Symbol	Conditions			Unit	
rarameter	Gymbol	Conditions	min	typ	max	Oilli
[Output Block]					1	
Output stage supply current	IBB-ON		0.9	1.3	1.7	mA
output stage supply current	IBB-OFF		0.52	0.7	1.05	m/
Output saturation voltage 1	V <sub>O</sub> (sat) 1	$I_{O} = +0.5 \text{ A (sink)}$		1.1	1.4	V
Output saturation voltage 2	V <sub>O</sub> (sat) 2	$I_{O} = +1.0 \text{ A (sink)}$		1.4	1.7	V
Output saturation voltage 3	V <sub>O</sub> (sat) 3	$I_O = -0.5 \text{ A (source)}$		1.9	2.2	V
Output saturation voltage 4	V <sub>O</sub> (sat) 4	$I_O = -1.0 \text{ A (source)}$		2.2	2.5	V
Output leakage current	I <sub>O</sub> 1 (leak)	$V_O = V_{BB}$ (sink)			50	μΑ
Output leakage current	I <sub>O</sub> 2 (leak)	V <sub>O</sub> = 0V (source)	-50			μΑ
Output sustain voltage	V <sub>SUS</sub>	L = 15 mH, I <sub>O</sub> = 1.0 A *	45			V
[Logic Block]						
	I <sub>CC</sub> ON	D0 = 1, D1 = 1, D2 = 1, D3 = 1 When these data values are set	24	35	46	m/
Logic system supply current	I <sub>CC</sub> OFF1	D0 = 0, D1 = 0, D2 = 0, D3 = 0	22	32	42	m/
	I <sub>CC</sub> OFF2	ST = LOW		0.05	0.1	m/
lancaturalta ara	V <sub>IH</sub>		2			V
nput voltage	$V_{IL}$				0.8	V
land the second second	I <sub>IH</sub>	V <sub>IH</sub> = 2 V			35	μΑ
nput current	I <sub>IL</sub>	V <sub>IL</sub> = 0.8 V	6			μΑ
		D0 = 1, D1 = 1, D2 = 1, D3 = 1 When these data values are set	0.470	0.50	0.525	V
		D0 = 1, D1 = 1, D2 = 1, D3 = 0	0.445	0.48	0.505	V
		D0 = 1, D1 = 1, D2 = 0, D3 = 1	0.425	0.46	0.485	V
		D0 = 1, D1 = 1, D2 = 0, D3 = 0	0.410	0.43	0.465	V
		D0 = 1, D1 = 0, D2 = 1, D3 = 1	0.385	0.41	0.435	V
		D0 = 1, D1 = 0, D2 = 1, D3 = 0	0.365	0.39	0.415	V
Sense voltages	VE	D0 = 1, D1 = 0, D2 = 0, D3 = 1	0.345	0.37	0.385	V
3		D0 = 1, D1 = 0, D2 = 0, D3 = 0	0.325	0.35	0.365	V
		D0 = 0, D1 = 1, D2 = 1, D3 = 1	0.280	0.30	0.325	V
		D0 = 0, D1 = 1, D2 = 1, D3 = 0	0.240	0.26	0.285	V
		D0 = 0, D1 = 1, D2 = 0, D3 = 1	0.195	0.22	0.235	V
		D0 = 0, D1 = 1, D2 = 0, D3 = 0	0.155	0.17	0.190	V
		D0 = 0, D1 = 0, D2 = 1, D3 = 1	0.115	0.13	0.145	V
		D0 = 0, D1 = 0, D2 = 1, D3 = 0	0.075	0.09	0.100	V
Reference current	I <sub>REF</sub>	V <sub>REF</sub> = 1.5 V	-0.5			μA
CR pin current	ICR	CR = 1.0 V	-1.6	-1.2	-0.8	m/
MD pin current	IMD	MD = 1.0 V, CR = 4.0 V	-5.0			μ/
Logic system on voltage	VLSDON		2.6	2.8	3.0	V
Logic system off voltage	VLSDOFF		2.45	2.65	2.85	V
J - /	_					V
LVSD hysteresis	VLHIS		0.03	0.15	0.35	v

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# AC Electrical Characteristics at $V_{CC}$ = 5 V

Parameter	Symbol	Conditions		Unit			
Farameter	Symbol	Conditions	min	typ	max	Offic	
Clock frequency	Fclk	V <sub>CC</sub> = 5.0 V		200	550	kHz	
Data setup time	T <sub>DS</sub>	V <sub>CC</sub> = 5.0 V	0.9	2.5		μS	
Data hold time	T <sub>DH</sub>	V <sub>CC</sub> = 5.0 V	0.9	2.5		μS	
Minimum clock high-level pulse width	T <sub>SCH</sub>	V <sub>CC</sub> = 5.0 V	0.9	2.5		μS	
Minimum clock low-level pulse width	T <sub>SCL</sub>	V <sub>CC</sub> = 5.0 V	0.9	2.5		μS	
SET pin stipulated time	Tlat	V <sub>CC</sub> = 5.0 V	0.9	2.5		μS	
SET pin signal pulse width	Tlatw	V <sub>CC</sub> = 5.0 V	1.9	5.0		μS	



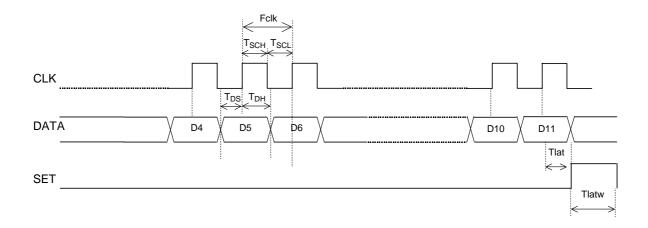
# LB11946

# Electrical Characteristics at Ta = 25°C, $V_{CC}$ = 3.3 V, $V_{BB}$ = 42 V, $V_{REF}$ = 1.0 V (When measuring the sense voltage: $V_{REF}$ = 1.03 V)

Parameter	Symbol	Conditions		Ratings		Unit
Falanielei	Symbol	Conditions	min	typ	max	Offic
[Output Block]						
Output stage supply current	I <sub>BB</sub> ON		0.9	1.3	1.7	mA
Output stage supply current	I <sub>BB</sub> OFF		0.52	0.7	1.05	mA
Output saturation voltage 1	V <sub>O</sub> (sat) 1	$I_{O} = +0.5 \text{ A (sink)}$		1.2	1.5	٧
Output saturation voltage 2	V <sub>O</sub> (sat) 2	$I_{O} = +1.0 \text{ A (sink)}$		1.5	1.8	V
Output saturation voltage 3	V <sub>O</sub> (sat) 3	$I_O = -0.5 \text{ A (source)}$		2.0	2.3	V
Output saturation voltage 4	V <sub>O</sub> (sat) 4	I <sub>O</sub> = -1.0 A (source)		2.3	2.6	V
Output leakage current	I <sub>O</sub> 1 (leak)	$V_O = V_{BB}$ (sink)			50	μΑ
Output leakage current	I <sub>O</sub> 2 (leak)	V <sub>O</sub> = 0 V (source)	-50			μΑ
Output sustain voltage	V <sub>SUS</sub>	L = 15 mH I <sub>O</sub> -1.5A *	45			٧
[Logic Block]						
	I <sub>CC</sub> ON	D0 = 1, D1 = 1, D2 = 1, D3 = 1 When these data values are set	21	30	39	mA
Logic system supply current	I <sub>CC</sub> OFF1	D0 = 0, $D1 = 0$ , $D2 = 0$ , $D3 = 0$	19	28	36.5	mA
	I <sub>CC</sub> OFF2	ST = 0.8 V		0.03	0.1	mA
Input voltage	V <sub>IH</sub>		2			V
input voltage	$V_{IL}$				0.8	V
Input current	I <sub>IH</sub>	V <sub>IH</sub> = 2 V			35	μΑ
input current	I <sub>IL</sub>	V <sub>IL</sub> = 0.8 V	6			μΑ
		D0 = 1, D1 = 1, D2 = 1, D3 = 1 V <sub>REF</sub> = 1.03 V	0.303	0.330	0.356	V
		D0 = 1, D1 = 1, D2 = 1, D3 = 0 V <sub>REF</sub> = 1.03 V	0.290	0.315	0.341	V
		D0 = 1, D1 = 1, D2 = 0, D3 = 1 V <sub>REF</sub> = 1.03 V	0.276	0.300	0.324	V
		D0 = 1, D1 = 1, D2 = 0, D3 = 0 V <sub>REF</sub> = 1.03 V	0.263	0.286	0.309	V
		D0 = 1, D1 = 0, D2 = 1, D3 = 1 V <sub>REF</sub> = 1.03 V	0.250	0.272	0.294	V
		$D0 = 1$ , $D1 = 0$ , $D2 = 1$ , $D3 = 0$ $V_{REF} = 1.03$ $V$	0.236	0.257	0.278	V
Sense voltages	VE	$D0 = 1$ , $D1 = 0$ , $D2 = 0$ , $D3 = 1$ $V_{REF} = 1.03$ $V$	0.223	0.243	0.263	V
Sense voltages	V L	$D0 = 1$ , $D1 = 0$ , $D2 = 0$ , $D3 = 0$ $V_{REF} = 1.03$ $V$	0.209	0.228	0.247	V
		$D0 = 0$ , $D1 = 1$ , $D2 = 1$ , $D3 = 1$ $V_{REF} = 1.03$ $V$	0.183	0.200	0.217	V
		D0 = 0, D1 = 1, D2 = 1, D3 = 0 V <sub>REF</sub> = 1.03 V	0.155	0.170	0.185	V
		$D0 = 0$ , $D1 = 1$ , $D2 = 0$ , $D3 = 1$ $V_{REF} = 1.03$ $V$	0.128	0.143	0.158	V
		D0 = 0, D1 = 1, D2 = 0, D3 = 0 V <sub>REF</sub> = 1.03 V	0.102	0.114	0.126	V
		$D0 = 0$ , $D1 = 0$ , $D2 = 1$ , $D3 = 1$ $V_{REF} = 1.03$ $V$	0.074	0.085	0.096	V
		$D0 = 0$ , $D1 = 0$ , $D2 = 1$ , $D3 = 0$ $V_{REF} = 1.03$ $V$	0.047	0.057	0.067	V
Reference current	I <sub>REF</sub>	V <sub>REF</sub> = 1.0 V	-0.5			μΑ
CR pin current	ICR	CR = 1.0 V	-0.91	-0.7	-0.49	mA
MD pin current	IMD	MD = 1.0 V, CR = 4.0V	-5.0			μΑ
LVSD voltage	VLSDON		2.6	2.8	3.0	V
Logic system off voltage	VLSDOFF		2.45	2.65	2.85	V
LVSD hysteresis	VLHIS		0.03	0.15	0.35	V
Thermal shutdown temperature	Ts	Design guarantee		170		°C

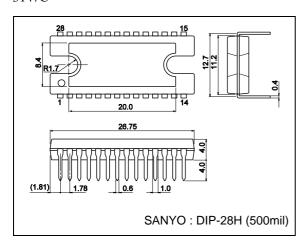
# AC Electrical Characteristics at $V_{CC} = 3.3 \text{ V}$

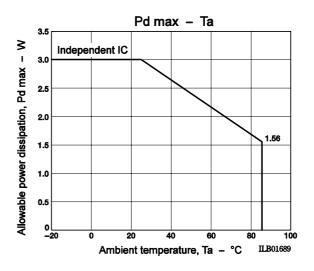
Parameter	Symbol	Conditions		Unit			
Falametei	Symbol	Conditions	min	typ	max	Offic	
Clock frequency	Fclk	V <sub>CC</sub> = 3.3 V		200	550	kHz	
Data setup time	T <sub>DS</sub>	V <sub>CC</sub> = 3.3 V	0.9	2.5		μS	
Data hold time	T <sub>DH</sub>	V <sub>CC</sub> = 3.3 V	0.9	2.5		μS	
Minimum clock high-level pulse width	T <sub>SCH</sub>	V <sub>CC</sub> = 3.3 V	0.9	2.5		μS	
Minimum clock low-level pulse width	T <sub>SCL</sub>	V <sub>CC</sub> = 3.3 V	0.9	2.5		μS	
SET pin stipulated time	Tlat	V <sub>CC</sub> = 3.3 V	0.9	2.5		μS	
SET pin signal pulse width	Tlatw	V <sub>CC</sub> = 3.3 V	1.9	5.0		μS	



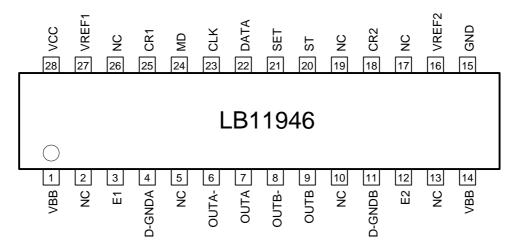
### **Package Dimensions**

unit: mm 3147C



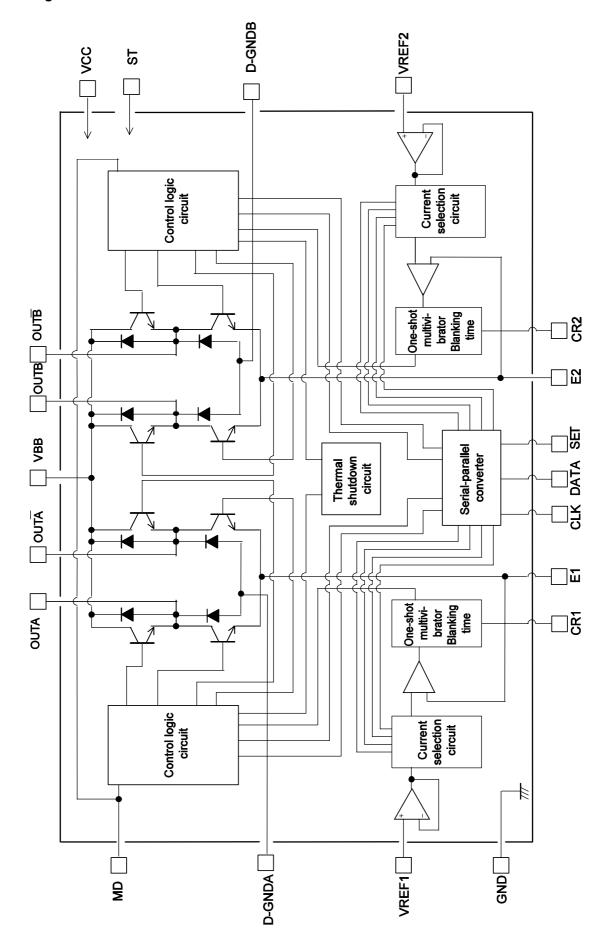


#### **Pin Assignment**

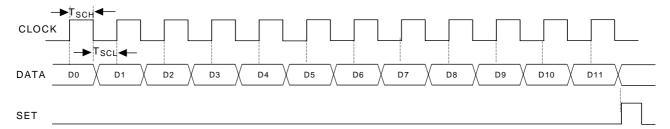


Note \*: The D-GNDA and D-GNDB pins are the anode sides of the lower side diodes.

### **Block Diagram**



# **Timing Chart**



### **Serially Transferred Data Definition**

	IA4	IA3	IA2	IA1	DE1	PH1	IB4	IB3	IB2	IB1	DE2	PH2		Output	mode		I/O	DEC
No.	D0	D1	D2	D3	D4	D5	D6	D7	D8	D9	D10	D11	OUTA	OUTA	OUTB	OUTB	ratio	MODE
0	1	1	1	1	1	1	1	1	1	1	1	1	Н	L	Н	L	100%	SLOW
1	1	1	1	0	1	1	1	1	1	0	1	1	Н	L	Н	L	96	SLOW
2	1	1	0	1	1	1	1	1	0	1	1	1	Н	L	Η	L	91	SLOW
3	1	1	0	0	1	1	1	1	0	0	1	1	Н	L	Η	L	87	SLOW
4	1	0	1	1	1	1	1	0	1	1	1	1	Н	L	Н	L	83	SLOW
5	1	0	1	0	1	1	1	0	1	0	1	1	Н	L	Η	L	78	SLOW
6	1	0	0	1	1	1	1	0	0	1	1	1	Н	L	Η	L	74	SLOW
7	1	0	0	0	1	1	1	0	0	0	1	1	Н	L	Н	L	70	SLOW
8	0	1	1	1	1	1	0	1	1	1	1	1	Н	L	Н	L	61	SLOW
9	0	1	1	0	1	1	0	1	1	0	1	1	Н	L	Η	L	52	SLOW
10	0	1	0	1	1	1	0	1	0	1	1	1	Н	L	Η	L	44	SLOW
11	0	1	0	0	1	1	0	1	0	0	1	1	Н	L	Н	L	35	SLOW
12	0	0	1	1	1	1	0	0	1	1	1	1	Н	L	Η	L	26	SLOW
13	0	0	1	0	1	1	0	0	1	0	1	1	Н	L	Η	L	17	SLOW
14	1	1	1	1	0	0	1	1	1	1	0	0	L	Н	L	Н	100	FAST
15	1	1	1	0	0	0	1	1	1	0	0	0	L	Η	L	Н	96	FAST
16	1	1	0	1	0	0	1	1	0	1	0	0	L	Η	L	Н	91	FAST
17	1	1	0	0	0	0	1	1	0	0	0	0	L	Н	L	Н	87	FAST
18	1	0	1	1	0	0	1	0	1	1	0	0	L	Η	L	Н	83	FAST
19	1	0	1	0	0	0	1	0	1	0	0	0	L	Η	L	Н	78	FAST
20	1	0	0	1	0	0	1	0	0	1	0	0	L	Н	L	Н	74	FAST
21	1	0	0	0	0	0	1	0	0	0	0	0	L	Н	L	Н	70	FAST
22	0	1	1	1	0	0	0	1	1	1	0	0	L	Н	L	Н	61	FAST
23	0	1	1	0	0	0	0	1	1	0	0	0	L	Н	L	Н	52	FAST
24	0	1	0	1	0	0	0	1	0	1	0	0	L	Н	L	Н	44	FAST
25	0	1	0	0	0	0	0	1	0	0	0	0	L	Н	L	Н	35	FAST
26	0	0	1	1	0	0	0	0	1	1	0	0	L	Н	L	Н	26	FAST
27	0	0	1	0	0	0	0	0	1	0	0	0	L	Н	L	Н	17	FAST
28	0	0	0	0	*	*	0	0	0	0	*	*	OFF	OFF	OFF	OFF	0	-

Note \*: Either 0 or 1.

Note \*1: In mixed decay mode, set D4 and D10 to 0 and set the MD pin to a level in the range 1.5 to 4.0 V.

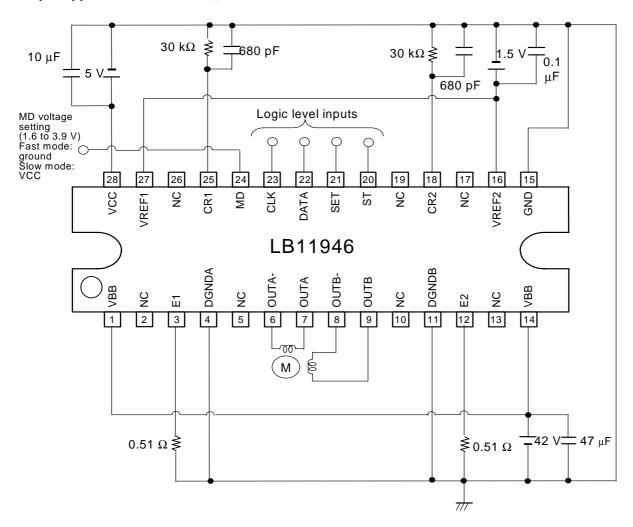
#### **Current Settings Truth Table**

Current Settings Truth Table \* Items in parentheses are defined by the serial data.

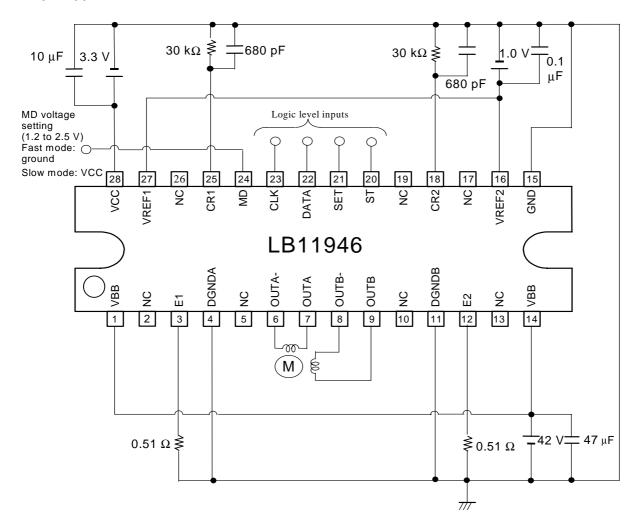
IA4 (D0)	IA3 (D1)	IA2 (D2)	IA1 (D3)	Set current lout	Current ratio (%)
1	1	1	1	11.5/11.5 × VREF/3.04RE = lout	100
1	1	1	0	11.0/11.5 × VREF/3.04RE = lout	95.65
1	1	0	1	10.5/11.5 × VREF/3.04RE = lout	91.30
1	1	0	0	10.0/11.5 × VREF/3.04RE = lout	86.95
1	0	1	1	9.5/11.5 × VREF/3.04RE = lout	82.61
1	0	1	0	9.0/11.5 × VREF/3.04RE = lout	78.26
1	0	0	1	8.5/11.5 × VREF/3.04RE = lout	73.91
1	0	0	0	8.0/11.5 × VREF/3.04RE = lout	69.56
0	1	1	1	7.0/11.5 × VREF/3.04RE = lout	60.87
0	1	1	0	6.0/11.5 × VREF/3.04RE = lout	52.17
0	1	0	1	5.0/11.5 × VREF/3.04RE = lout	43.48
0	1	0	0	4.0/11.5 × VREF/3.04RE = lout	34.78
0	0	1	1	3.0/11.5 × VREF/3.04RE = lout	26.08
0	0	1	0	2.0/11.5 × Vref/3.04RE = lout	17.39

Note \*: The current ratios shown are calculated values.

### Sample Application Circuit at $V_{CC} = 5 \text{ V}$



### Sample Application Circuit at $V_{CC} = 3.3 \text{ V}$



#### **Switching Off Time and Noise Canceller Time Calculations**

Notes on the CR Pin Setting (switching off time and noise canceller time)

The noise canceller time (Tn) and the switching off time (Toff) are set using the following formulas.

• When V<sub>CC</sub> is 5 V

Noise canceller time (Tn)

 $Tn \approx C \cdot R \cdot ln\{(1.5-RI)/(4.0-RI)\}[s]$ 

CR pin charge current: 1.25 mA

Switching off time (Toff)

Toff  $\approx -C \cdot R \cdot \ln (1.5/4.8)[s]$ 

Component value ranges

R:  $5.6 \text{ k}\Omega$  to  $100 \text{ k}\Omega$ C: 470 pF to 2000 pF

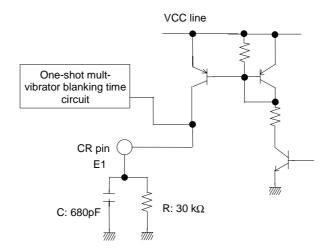
• When V<sub>CC</sub> is 3.3 V

Noise canceller time (Tn)

 $Tn \approx C \cdot R \cdot ln \{ (1.06 - RI) / (2.66 - RI) \} [s]$ 

CR pin charge current: 0.7 mA

Switching off time (Toff) Toff  $\approx -\text{C}\cdot\text{R}\cdot\text{ln} (1.06/3.1)[\text{s}]$ 



CR Pin Internal Circuit Structure

#### Notes on the MD Pin

- If slow decay mode is set up by setting the D4 and D10 bits in the input serial data to 1, the MD pin must be shorted to ground.
- If fast decay mode is set up by setting the D4 and D10 bits in the input serial data to 0, mixed decay mode can be set with the MD pin.

When the  $V_{CC} = 5$  V specifications are used the setting voltage range for mixed decay mode is 1.6 to 3.9 V.

When the  $V_{CC} = 3.3 \text{ V}$  specifications are used the setting voltage range for mixed decay mode is 1.2 to 2.5 V.

If mixed decay mode will not be used with the fast decay mode setting, either:

- (a) Short the MD pin to ground to select fast decay mode, or
- (b) Short the MD pin to  $V_{CC}$  to select slow decay mode.

#### **Usage Notes**

• Notes on the V<sub>REF</sub> pin

Since the  $V_{REF}$  pin inputs the reference voltage used to set the current, applications must be designed so that noise does not occur at this pin.

• Notes on the ground pins

Since this IC switches large currents, care is required with respect to the ground pins.

The PCB pattern in sections where large currents flow must be designed with low impedances and must be kept separate from the small-signal system.

In particular, the ground terminals of the E1 and E2 pin sense resistors (RE) and the external Schottky barrier diode ground terminals must be located as close as possible to the IC ground. The capacitors between  $V_{CC}$  and ground and between  $V_{BB}$  and ground must be as close as possible to the corresponding  $V_{CC}$  and  $V_{BB}$  pin in the pattern.

• Power on sequence

When turning the power systems on

 $V_{CC} \rightarrow logic$  level inputs (CLK, DATA, SET, and ST)  $\rightarrow VREF \rightarrow V_{BB}$ 

When turning the power systems off

 $V_{BB} \rightarrow VREF \rightarrow logic level inputs (CLK, DATA, SET, and ST) \rightarrow V_{CC}$ 

Note that if the power supply for the logic level inputs is on when the  $V_{CC}$  power supply is off, a bias with an unstable state will be applied due to the protection diodes at the  $V_{CC}$  pins, and this can cause incorrect operation.

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